

For EMI Filtering and ESD Protection.

FEATURES

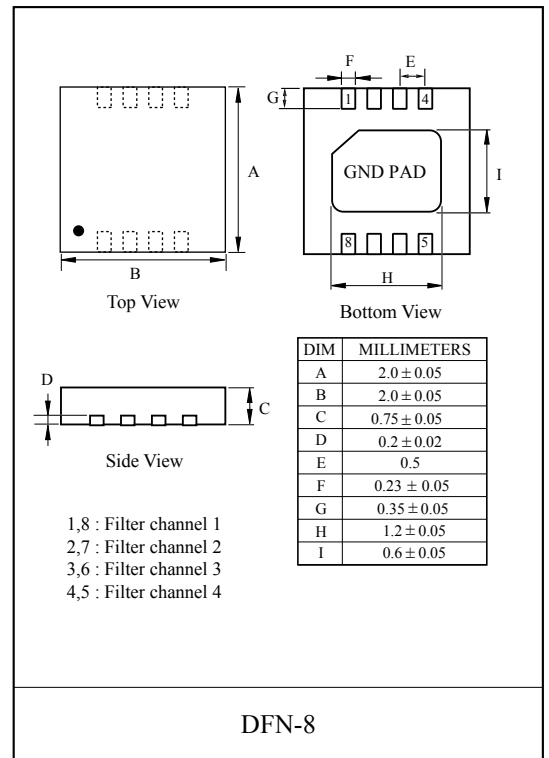
- EMI/RFI filtering.
- ESD Protection to IEC 61000-4-2 Level 4.
- Low insertion loss.
- Good attenuation of high frequency signals.
- Low clamping voltage.
- Low operating and leakage current.
- Four elements in one package

APPLICATIONS

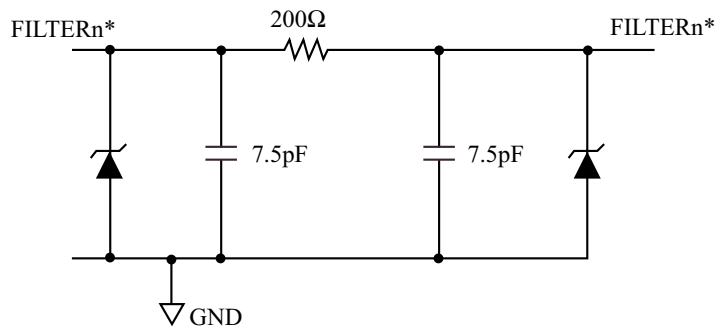
- Cell phone handsets.
- RF communications equipment.

MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Power Dissipation	P_D	300	mW
Operating Temperature	T_j	-55 ~ 150	°C
Storage Temperature	T_{stg}	-55 ~ 150	°C



EQUIVALENT CIRCUIT

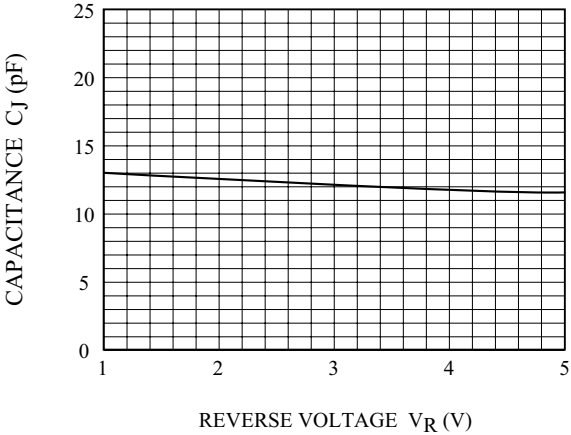


ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Stand-Off Voltage	V_{RWM}	-	-	-	5	V
Reverse Breakdown Voltage	V_{BR}	$I_t=1mA$	6	-	-	V
Reverse Leakage Current	I_R	$V_{RWM}=3V$	-	-	0.1	μA
Cutoff Frequency	f_{3dB}	$V_R=0V, Z_{SOURCE}=50 \Omega, Z_{LOAD}=50 \Omega$	-	210	-	MHz
Attenuation Frequency	f_{25dB}	$V_R=0V, Z_{SOURCE}=50 \Omega, Z_{LOAD}=50 \Omega$	800	-	3,000	MHz
Resistance	R	Between Input and Output	-	200	-	Ω
Capacitance	C	$V_R=2.5V, \text{ Between I/O Pins and GND}$	-	15	-	pF

PF2007DF8

$C_J - V_R$



$S_{21} - f$

